

# 12. Single-end operational amplifier

Kanazawa University  
Microelectronics Research Lab.  
Akio Kitagawa

# 12.1 Specification of OPA

# Parameters of OPA

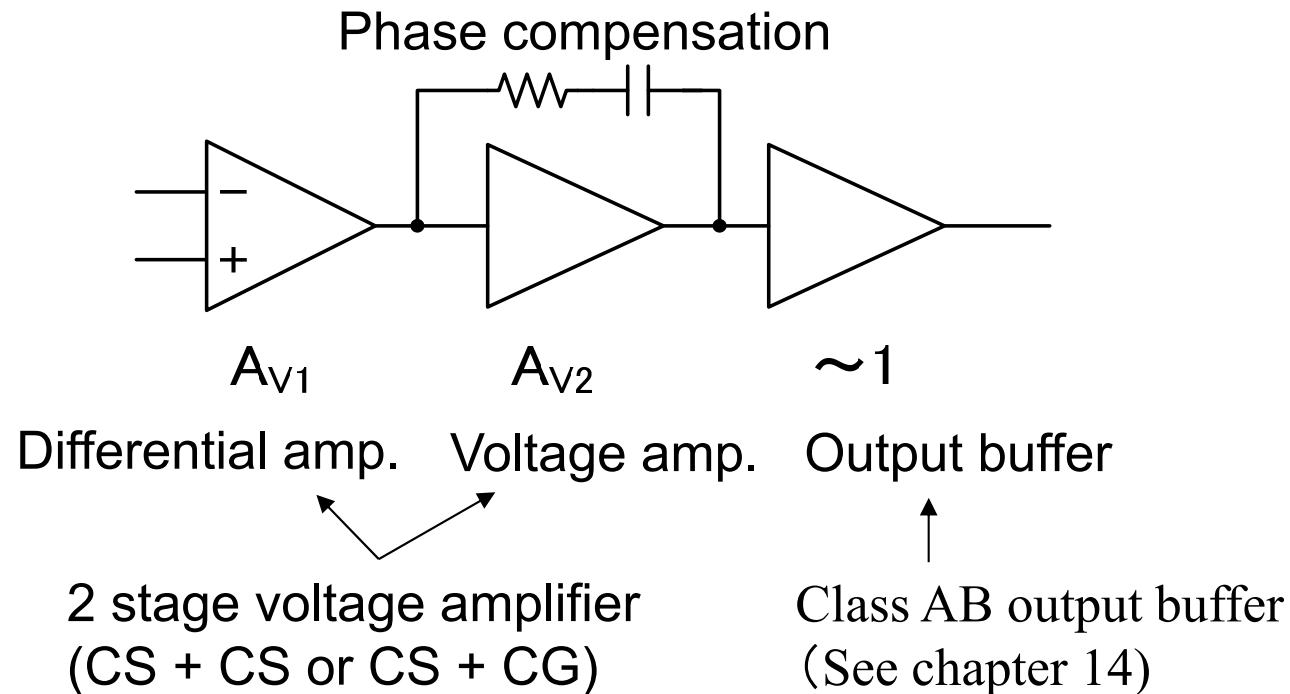
Parameter	Design constraint	Description
VDD (V)	max/typ/min	Power supply voltage
$I_{\text{Bias}}$ (uA)	max	Total bias current
Open loop gain $A_d$ (dB)	min	Differential gain
Sampling frequency $f_s$ (Hz)	max	For discrete CMFB OPA
GBP (Hz)	min	Unity gain frequency
SR (V/us)	min	$\gg 2 \cdot V_{\text{DD}}/f_s$
Settling time (us)	max	$< 2/f_s$
Phase margin (deg)	min	$> 60$ deg.
Common-mode input range (V)	min/max	
Output swing (V)	min/max	$>$ Differential input range
Input-referred noise level (uV @Hz)	max	In frequency range
Input-referred offset $V_{\text{OS}}$ (V)	max	
CMRR (dB)	min	Common Mode Rejection Ratio
PSRR (dB)	min	Power Supply Rejection Ratio
Load resistance, capacitance (ohm, F)	typ	Possible external load

# Sample Format of specification sheet

Parameter	Target value	Simulation			Measured value			Unit	Comment
		min.	typ.	max.	min.	typ.	max.		
VDD	1.8							V	
Bias current	312							uA	No input
Open loop gain	82							dB	
GBP	320M							Hz	Load=100fF
SR	244							V/us	Load=100fF
Settling time	24n							us	Error 1%
CMRR	-185							dB	
PSRR	-150							dB	
Noise level	50							nV/Hz <sup>0.5</sup>	@1MHz
Common-mode input range	upper	-0.5						V	
	lower	0.9						V	

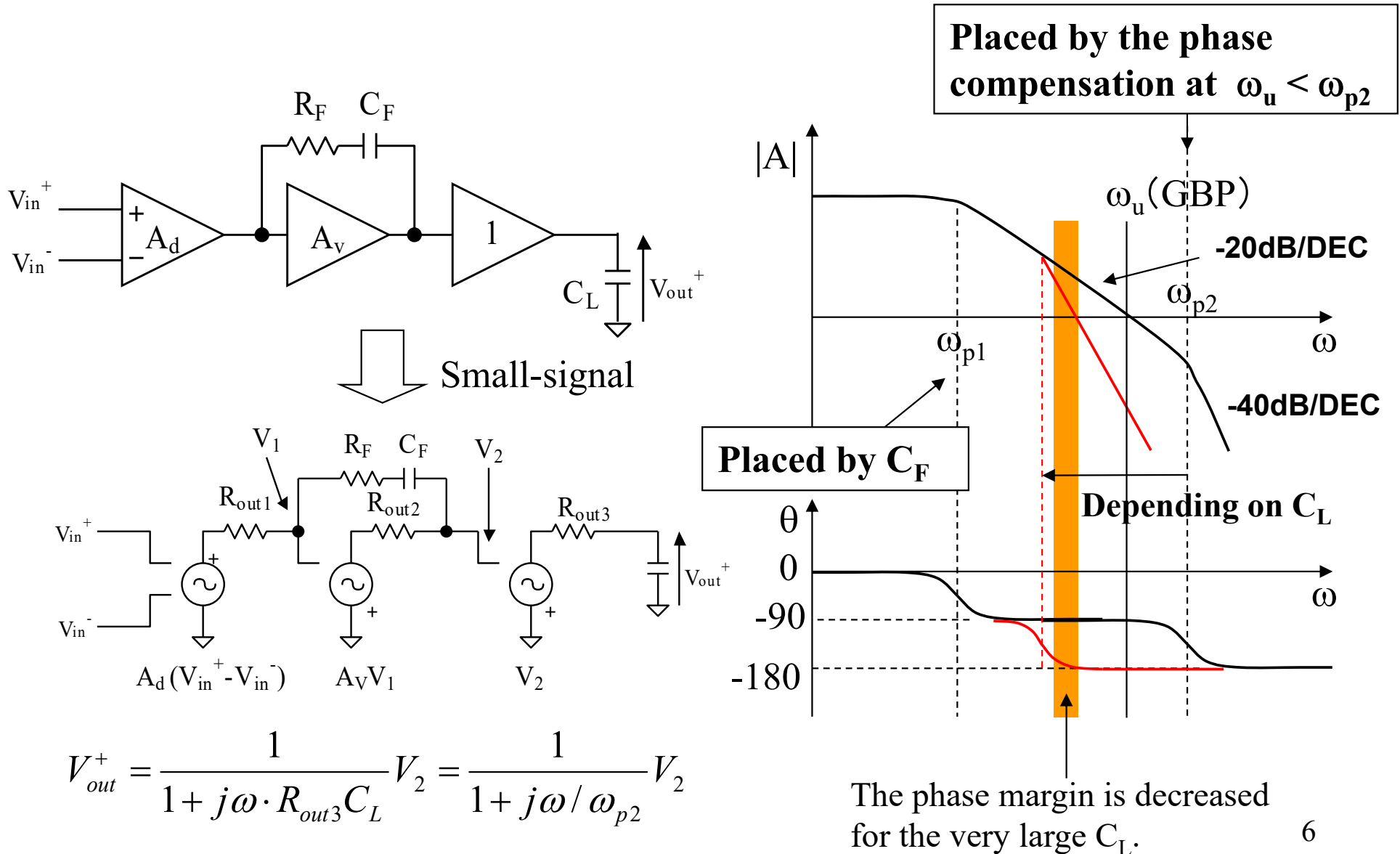
↑  
Estimated from the host system of the circuit

# Circuit configuration of OPA



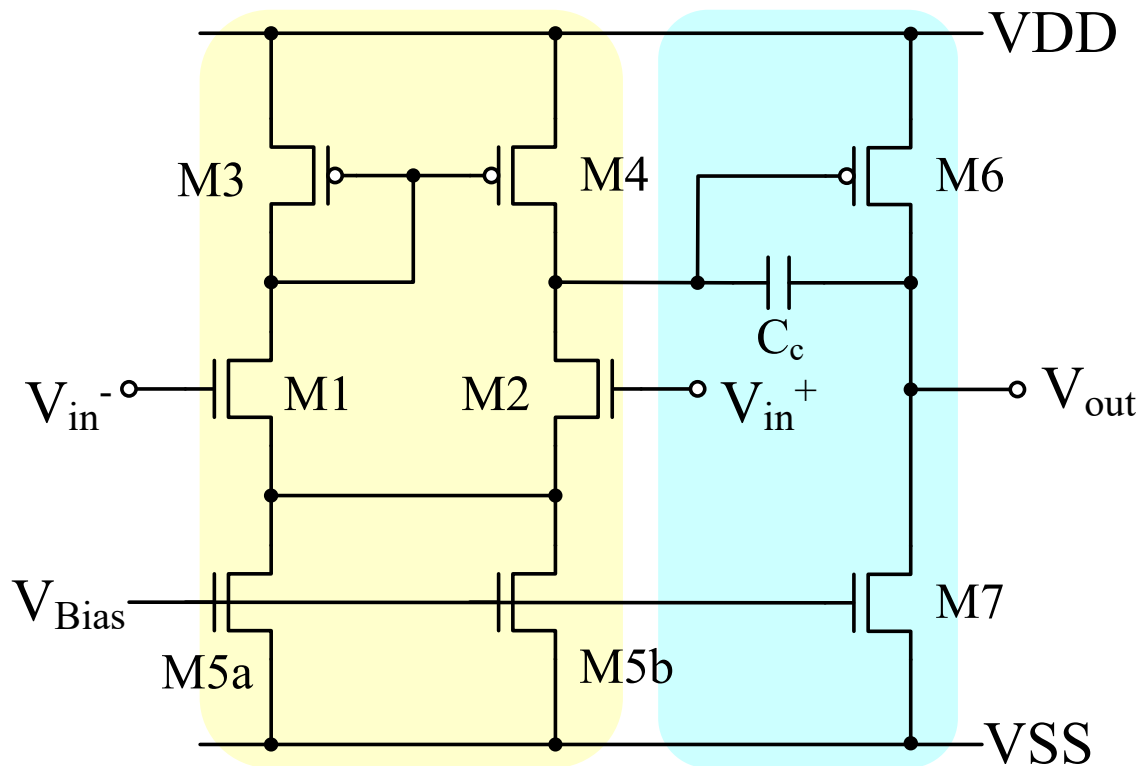
The output buffer may be omitted to reduce the power consumption, if the OPA drive only the capacitive load or operate with high loop gain.

# AC characteristic of OPA



# 12.2 Analysis of 2-stage CS OPA

# Structure of 2-stage OPA



Differential amplifier

CS amplifier

(without the output  
buffer)

$$A_d = g_{m1} \cdot (r_{ds2} \parallel r_{ds4}) \cdot g_{m6} \cdot (r_{ds6} \parallel r_{ds7})$$



# Bias current dependence of the differential gain

Differential amplifier stage

$$A_{V1} = -g_{m1} \cdot (r_{ds2} // r_{ds4})$$

$$g_{m1} = \sqrt{2\beta_1 I_{DS1}}$$

$$r_{ds2} = \frac{1}{\lambda_2 I_{DS2}} = \frac{1}{\lambda_2 I_{DS1}}$$

$$r_{ds4} = \frac{1}{\lambda_4 I_{DS4}} = \frac{1}{\lambda_4 I_{DS1}}$$

CS amplifier stage

$$A_{V2} = -g_{m6} \cdot (r_{ds6} // r_{ds7})$$

$$g_{m6} = \sqrt{2\beta_6 I_{DS6}}$$

$$r_{ds6} = \frac{1}{\lambda_6 I_{DS6}} = \frac{1}{\lambda_6 I_{DS6}}$$

$$r_{ds7} = \frac{1}{\lambda_7 I_{DS7}} = \frac{1}{\lambda_7 I_{DS6}}$$

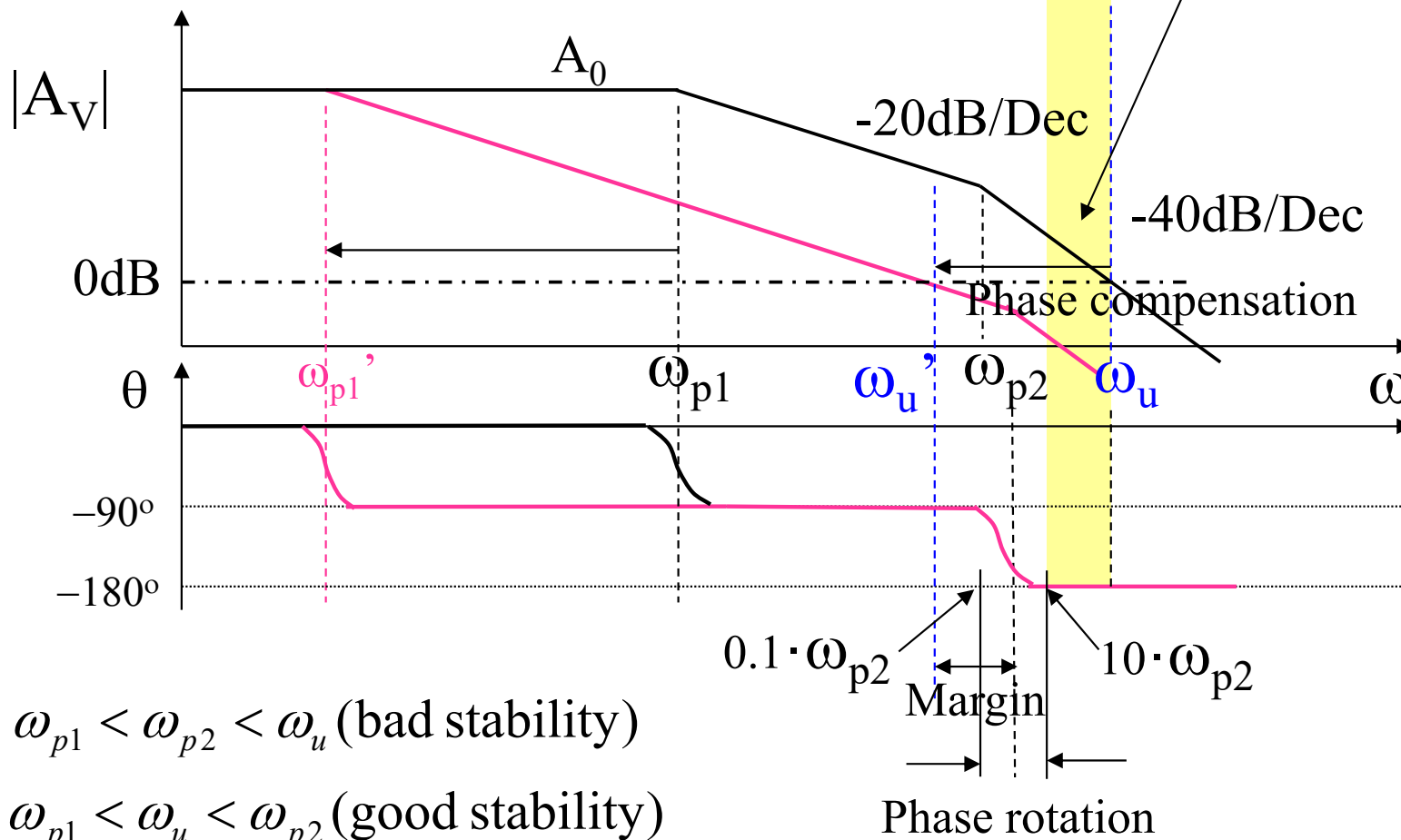
Total gain

$$A_d = A_{V1} A_{V2} = \frac{g_{m1} g_{m6}}{(g_{ds2} + g_{ds4})(g_{ds6} + g_{ds7})} = \frac{2\sqrt{\beta_1 \beta_6}}{(\lambda_2 + \lambda_4)(\lambda_6 + \lambda_7)} \frac{1}{\sqrt{I_{DS1} I_{DS6}}}$$

# Phase compensation (1)

Constraint for  $\omega_{p2}$  and  $\omega_u$

Cannot be used for the NFB circuit



$\omega_{p1} < \omega_{p2} < \omega_u$  (bad stability)

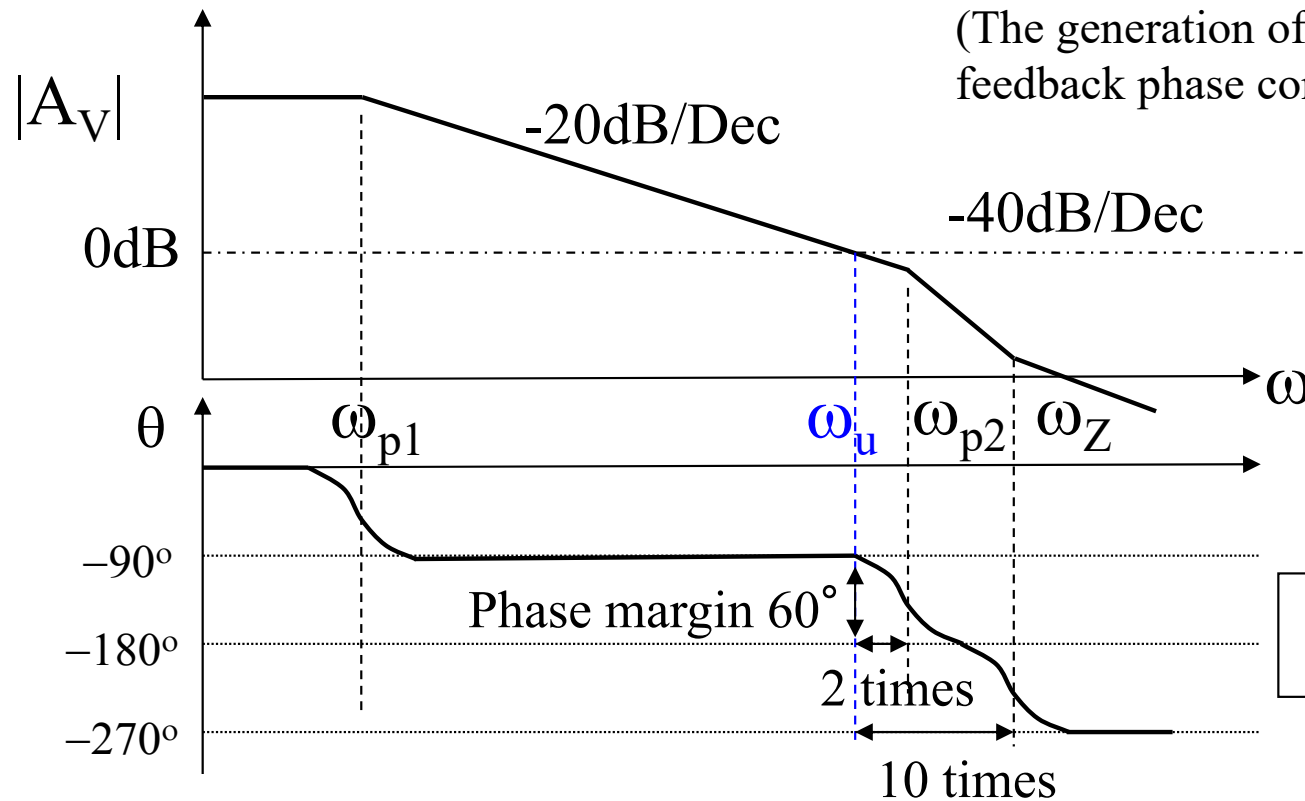
$\omega_{p1} < \omega_u < \omega_{p2}$  (good stability)

# Phase compensation (2)

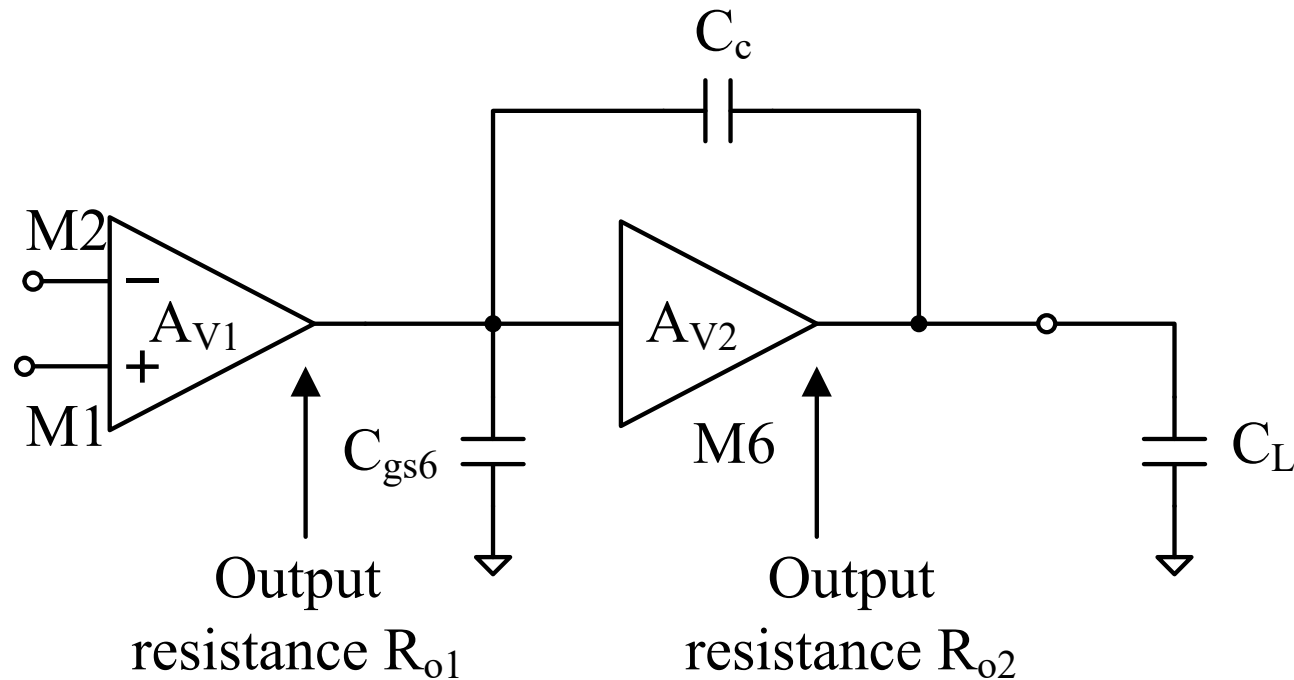
Constraint for  $\omega_z$  and  $\omega_u$

Constraint for  $\omega_{p2}$  and  $\omega_z$   $\left\{ \begin{array}{l} \omega_{p2} \geq 2 \cdot \omega_u \\ \omega_z \geq 10 \cdot \omega_u \end{array} \right.$

(The generation of zero is inevitable in the feedback phase compensation circuit.)



# Miller capacitance phase compensation technique



The input parasitic capacitance of M6 is  $C_{gs6}$ , but the input capacitance of the 2nd amplifier is controlled by the Miller capacitance  $C_M$ .

$$C_M = A_{V2} \cdot C_C + C_{gs6} \approx A_{V2} \cdot C_C$$

# Design of the frequency response

Pole and Zero frequency and the circuit parameters

$$\omega_{p1} \cong \frac{1}{(A_{V2} C_C) \cdot R_{o1}} \quad (\text{Miller effect})$$

$$\omega_u \cong A_{V1} \cdot A_{V2} \cdot \omega_{p1} = \frac{A_{V1}}{C_C \cdot R_{o1}} = \frac{g_{m1}}{C_C} \quad (\text{Miller effect})$$

$$\omega_Z \cong \frac{g_{m6}}{C_C} \quad (\text{Feed forward through } C_C)$$

$$\omega_{p2} \cong \frac{1}{C_L \cdot R_{o2}} \cong \frac{g_{m6}}{C_L} \quad (\text{The output capacitance of 2nd amplifier})$$

In the frequency range more than  $\omega_u$ , the input signal and output signal level is comparable, approximately,  $A_{V2} = G_{m2} \cdot R_{o2} = -g_{m6} \cdot R_{o2} \doteq -1$ .

# Constraint of the phase compensation

60° Phase margin

$$\omega_{p2} > 2\omega_u$$

$$\frac{g_{m6}}{C_L} > 2 \frac{g_{m1}}{C_C}$$

Separation between  $\omega_z$  and  $\omega_u$

$$\omega_z > 10\omega_u$$

$$\frac{g_{m6}}{C_C} > 10 \frac{g_{m1}}{C_C}$$

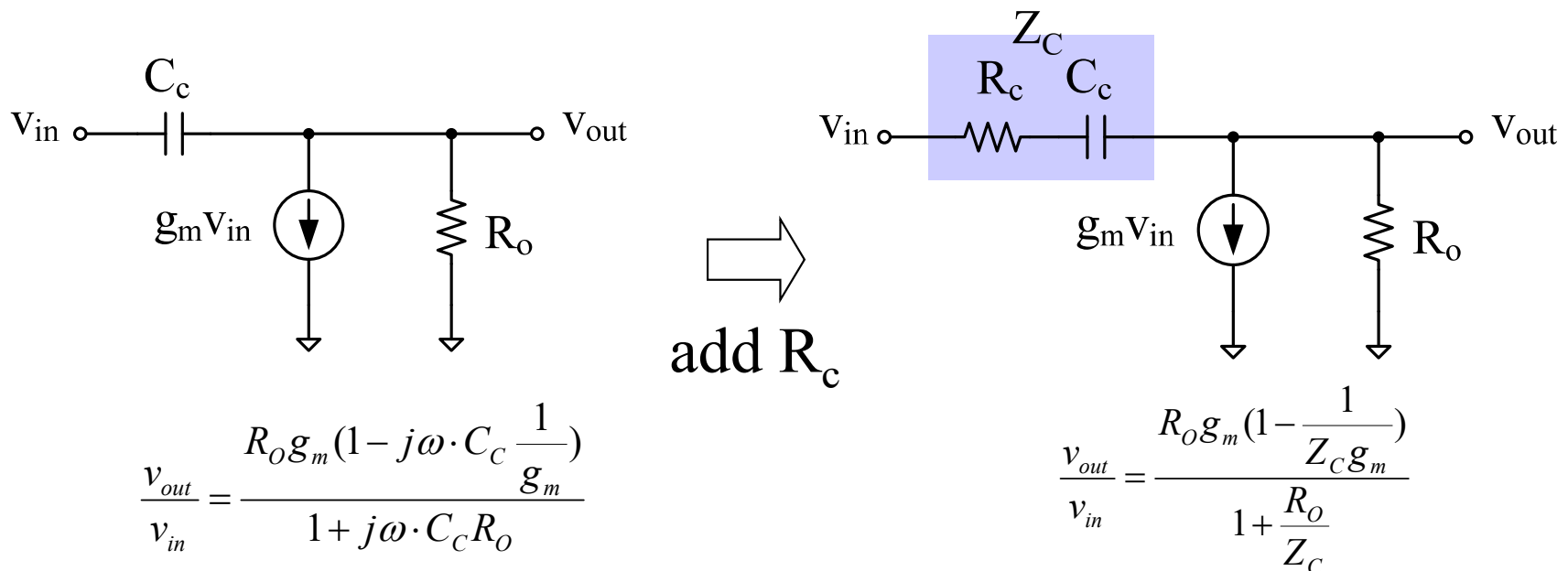
Phase compensation  
Constraint

$$g_{m6} \geq 10g_{m1}$$

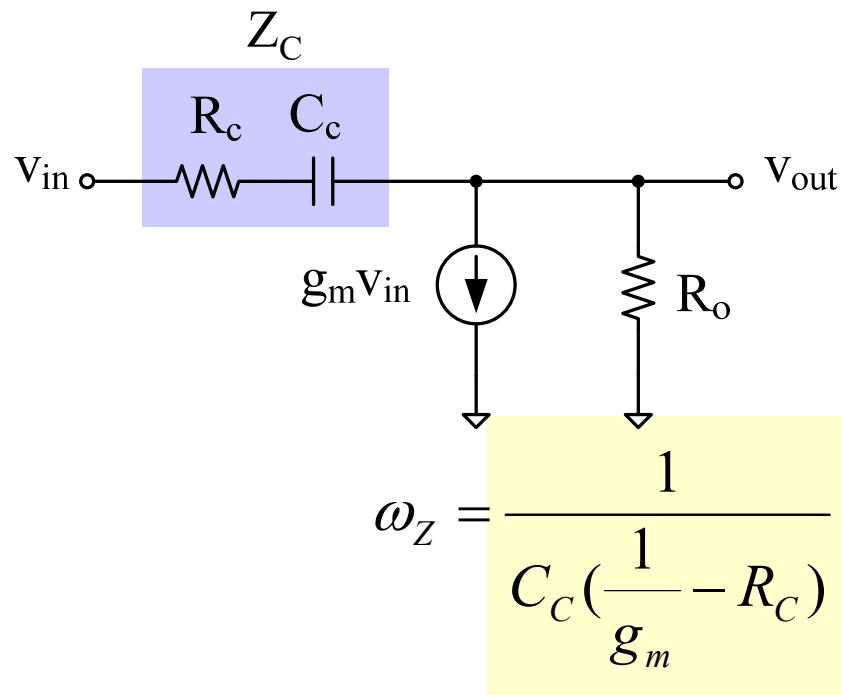
$$C_C \geq 0.2C_L$$

# Location of the zero (1)

The phase compensation using  $C_C$  requires the constraint  $g_{m6} > 10g_{m1}$  to remove the influence of  $\omega_Z$ . this method requires the very large  $g_{m6}$ . RC phase compensation can be used to evade this problem.



# Location of the zero (2)



$$\begin{aligned} \frac{v_{out}}{v_{in}} &= \frac{-R_O g_m \left( 1 - \frac{1}{Z_C g_m} \right)}{1 + \frac{R_O}{Z_C}} \\ &= \frac{-R_O g_m \left\{ 1 - j\omega \cdot C_C \left( \frac{1}{g_m} - R_C \right) \right\}}{1 + j\omega \cdot C_C (R_O + R_C)} \\ &= \frac{-R_O g_m \{ 1 - j\omega / \omega_Z \}}{1 + j\omega / \omega_{p3}} \end{aligned}$$

Method (1) : If  $R_C = 1/g_m$ ,  $\omega_Z \rightarrow \infty$  (Nulling the zero)

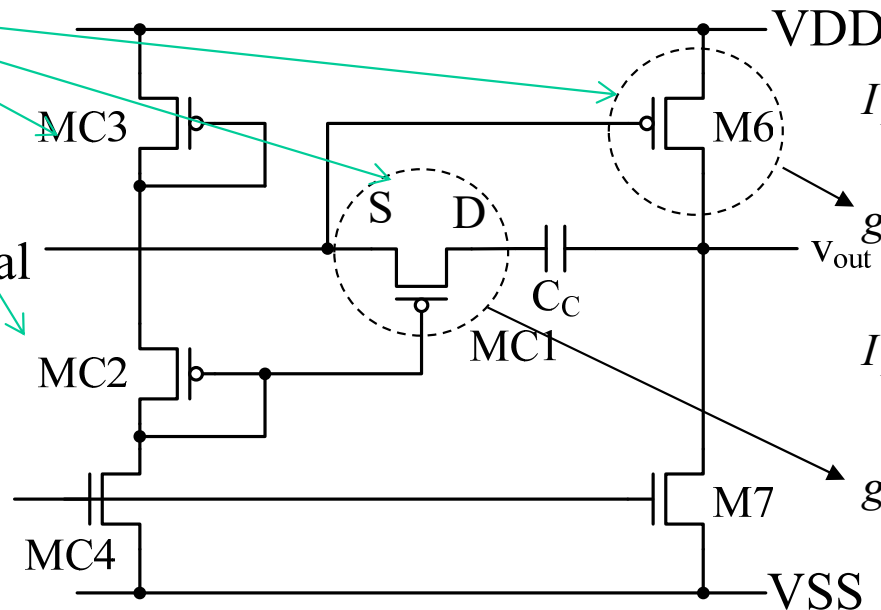
Method (2) : If  $R_C > 1/g_m$ ,  $\omega_Z$  is located in the left half plane (the phase turns counterclockwise.)



# Practical $R_c$ implementation by MOSFET output conductance

Same size

From Differential Amp.



$$I_{DS6} = \frac{\beta_p}{2} (V_{GS6} - V_{Tp})^2$$

$$g_{m6} = \frac{\partial I_{DS6}}{\partial V_{GS6}} = \beta_p (V_{GS6} - V_{Tp})$$

$$I_{DS\_MC1} = \beta_p \left\{ (V_{GS\_MC1} - V_{Tp}) V_{DS\_MC1} - \frac{1}{2} V_{DS\_MC1}^2 \right\}$$

$$g_{ds\_MC1} = \left. \frac{\partial I_{DS\_MC1}}{\partial V_{DS\_MC1}} \right|_{V_{DS\_MC1}=0} = \beta_p (V_{GS\_MC1} - V_{Tp})$$

M7 and MC4 are the same size.

M6, MC1, MC2, and MC3 are the same size.

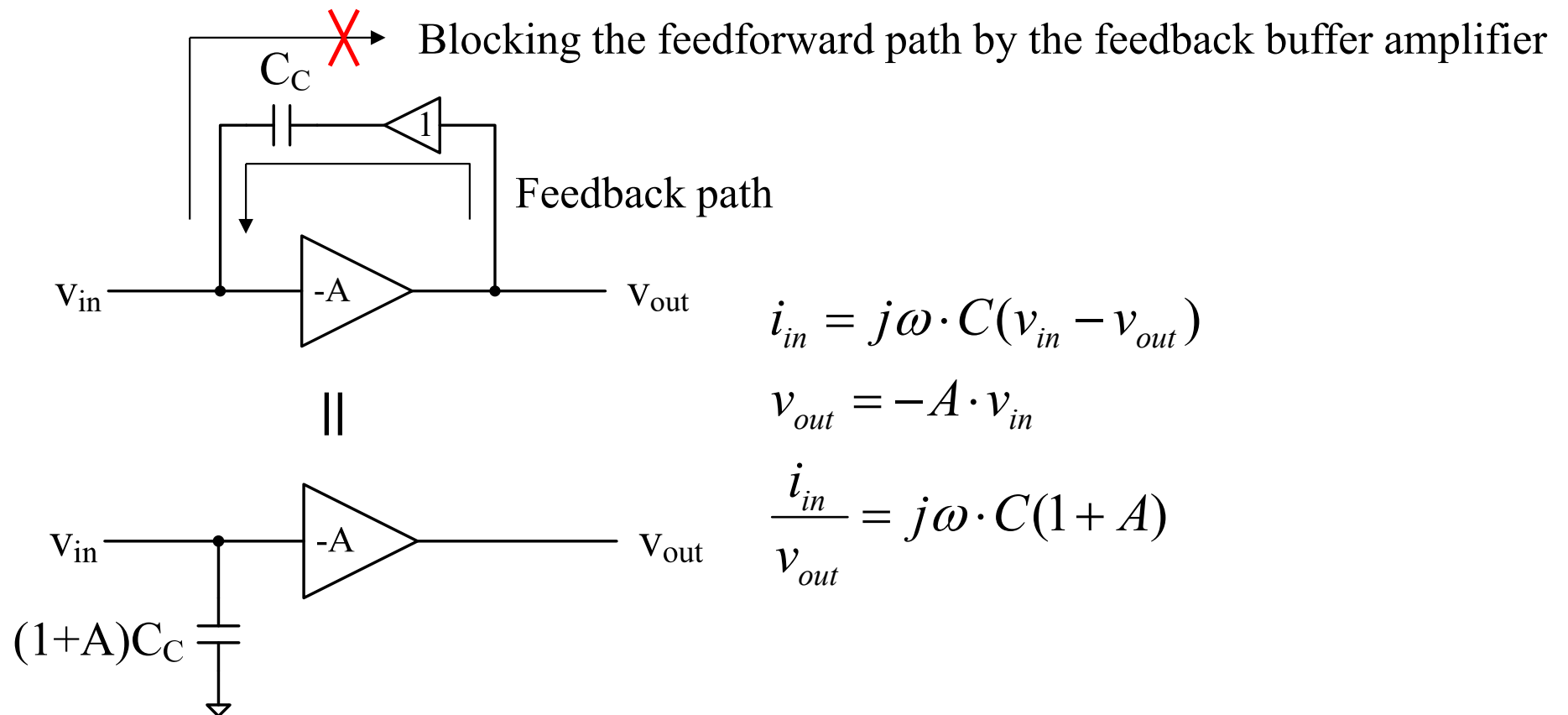
$$g_{m6} = g_{ds\_MC1}, \omega_z \rightarrow \infty$$

(see slide 16)

$$V_{GS\_MC3} + V_{GS\_MC2} = V_{GS6} + V_{GS\_MC1}$$

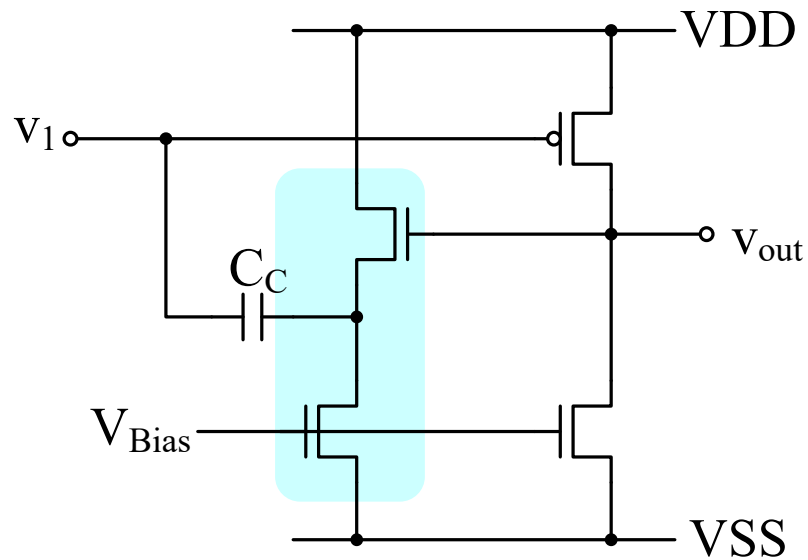
$$V_{GS\_MC1} = V_{GS\_MC3} + V_{GS\_MC2} - V_{GS6} = V_{GS6} + V_{GS6} - V_{GS6} = V_{GS6}$$

# Indirect phase compensation (1)

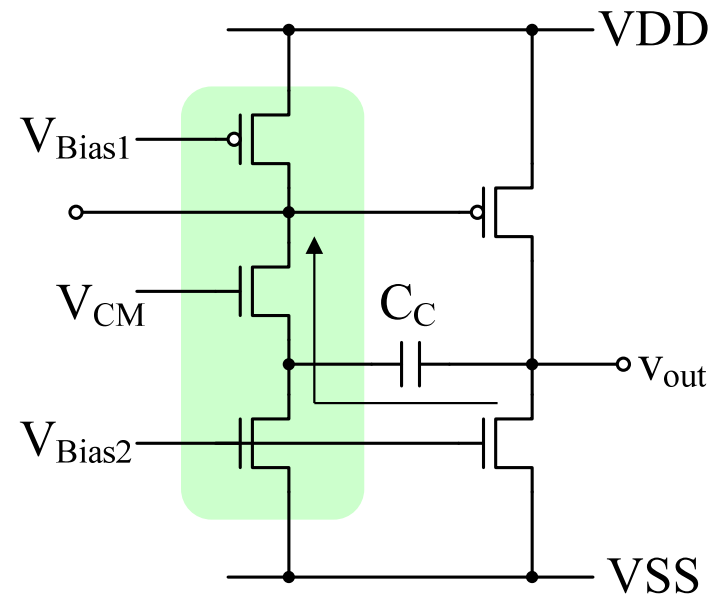


# Indirect phase compensation (2)

Source follower feedback buffer



Common-gate feedback buffer



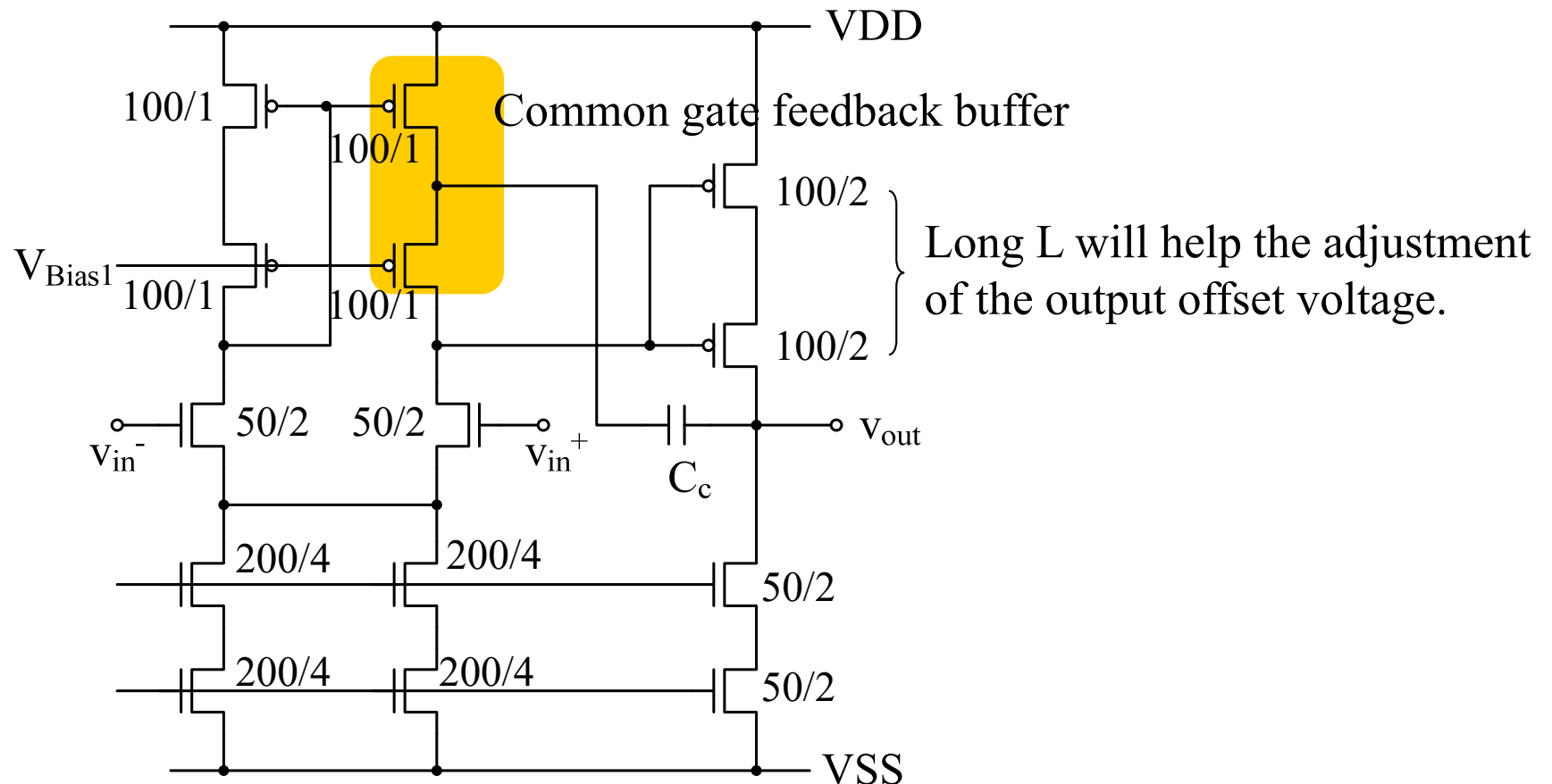
Advantages:

- High SR, High  $\omega_{p2}$ , High  $\omega_u$ , small  $C_c$

Disadvantage:

- Additional power consumption

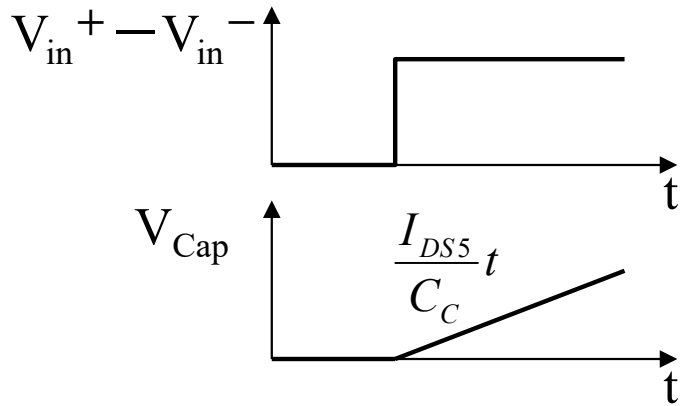
# Indirect phase compensation (3)



The cascode current mirror load is used in place of the feedback buffer. There is no additional power consumption.

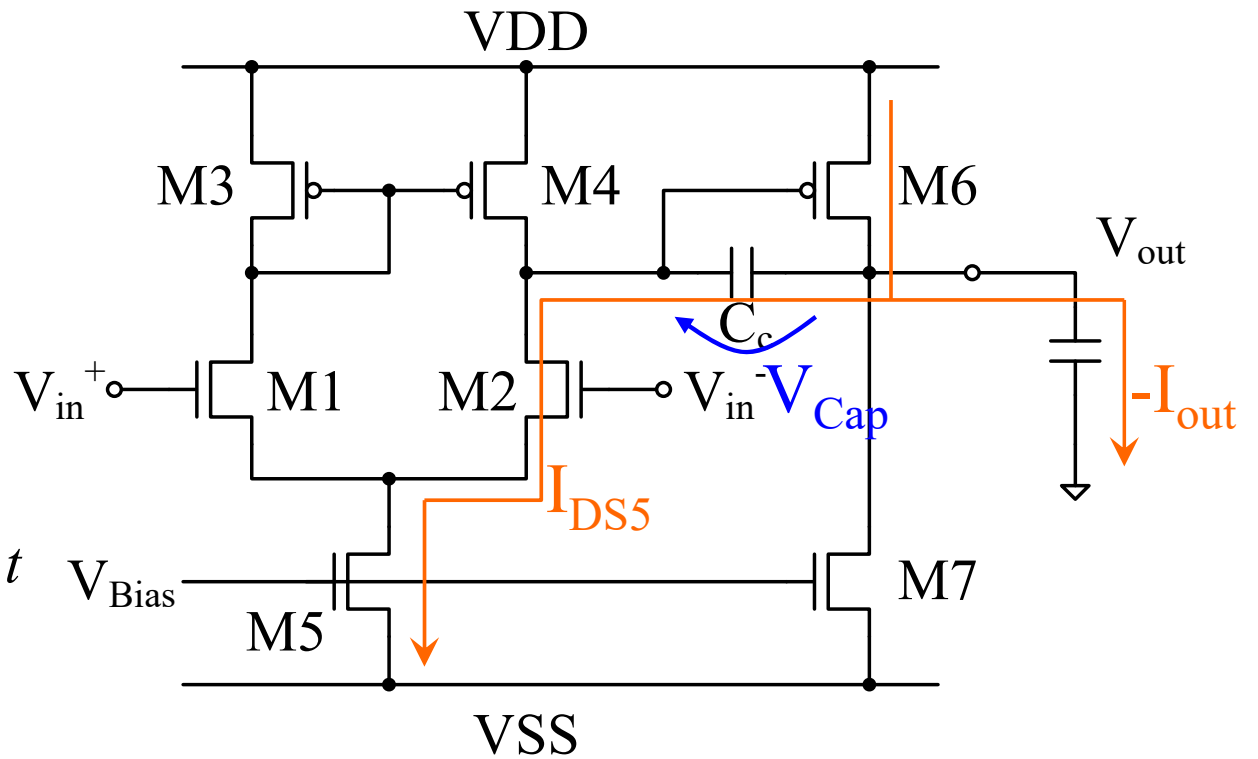
# 12.3 Optimization of MOSFET size

# $I_{SS}$ and SR



$$V_{Cap} = \frac{1}{C_C} \int I_{DS5} dt = \frac{I_{DS5}}{C_C} \cdot t$$

$$SR = \frac{I_{DS5}}{C_C}$$



SR is limited by the current  $I_{SS}$  ( $I_{DS5}$ ) and  $I_{out}$ .

# Saturation of M4 (1)

$$V_{DS3} \geq V_{GS3} - V_{Tp} = \Delta_{OV3}$$

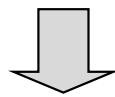
M3 always operates in the saturation region.

$$V_{DS4} = V_{GS6}$$

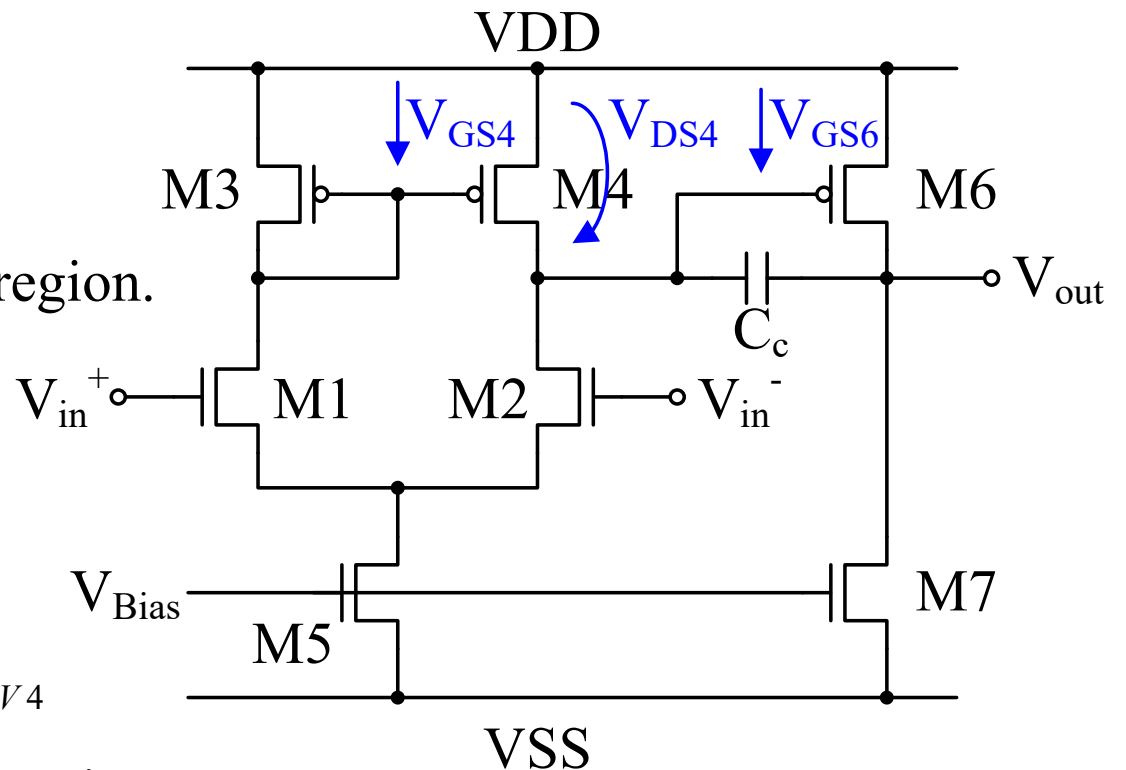
If  $V_{GS4} = V_{GS6}$ ,

$$V_{DS4} = V_{GS6} = V_{GS4} \geq V_{GS4} - V_{Tp} = \Delta_{OV4}$$

M4 always operates in the saturation region.



MOSFET size should be optimized for  $V_{GS4} = V_{GS6}$ .



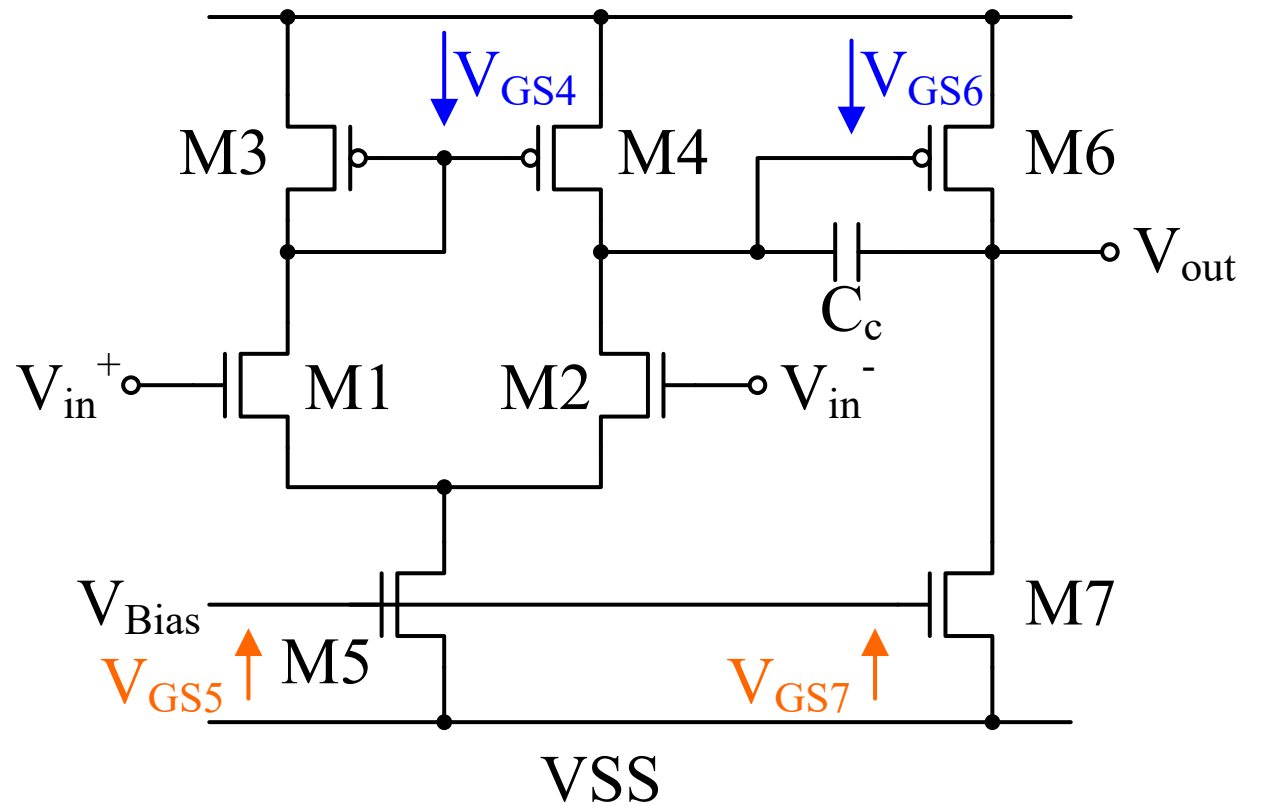
# Saturation of M4 (2)

If  $V_{GS4} = V_{GS6}$ ,

$$\frac{I_{DS6}}{I_{DS4}} = \frac{\left(\frac{W}{L}\right)_6}{\left(\frac{W}{L}\right)_4}$$

$V_{GS5} = V_{GS7}$

$$\frac{I_{DS7}}{I_{DS5}} = \frac{\left(\frac{W}{L}\right)_7}{\left(\frac{W}{L}\right)_5}$$





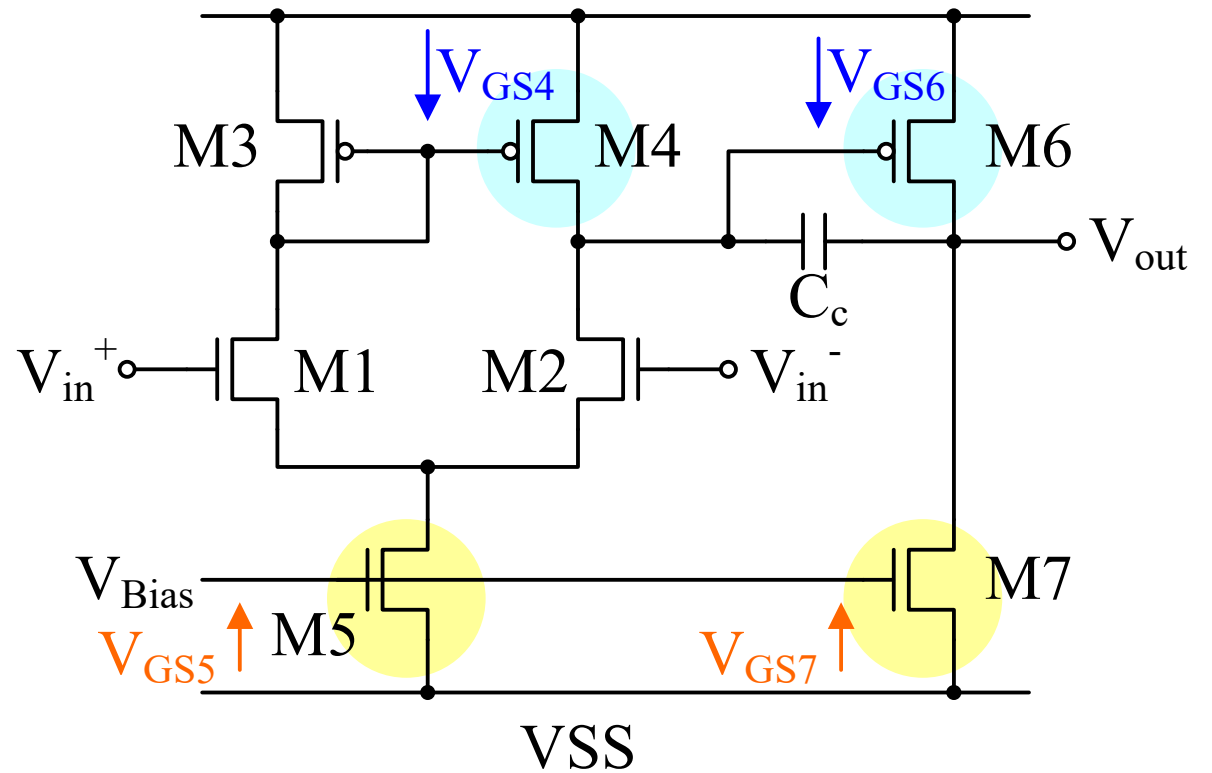
# Saturation of M4 (3)

$$\begin{cases} I_{DS6} = I_{DS7} \\ I_{DS5} = 2I_{DS4} \end{cases}$$

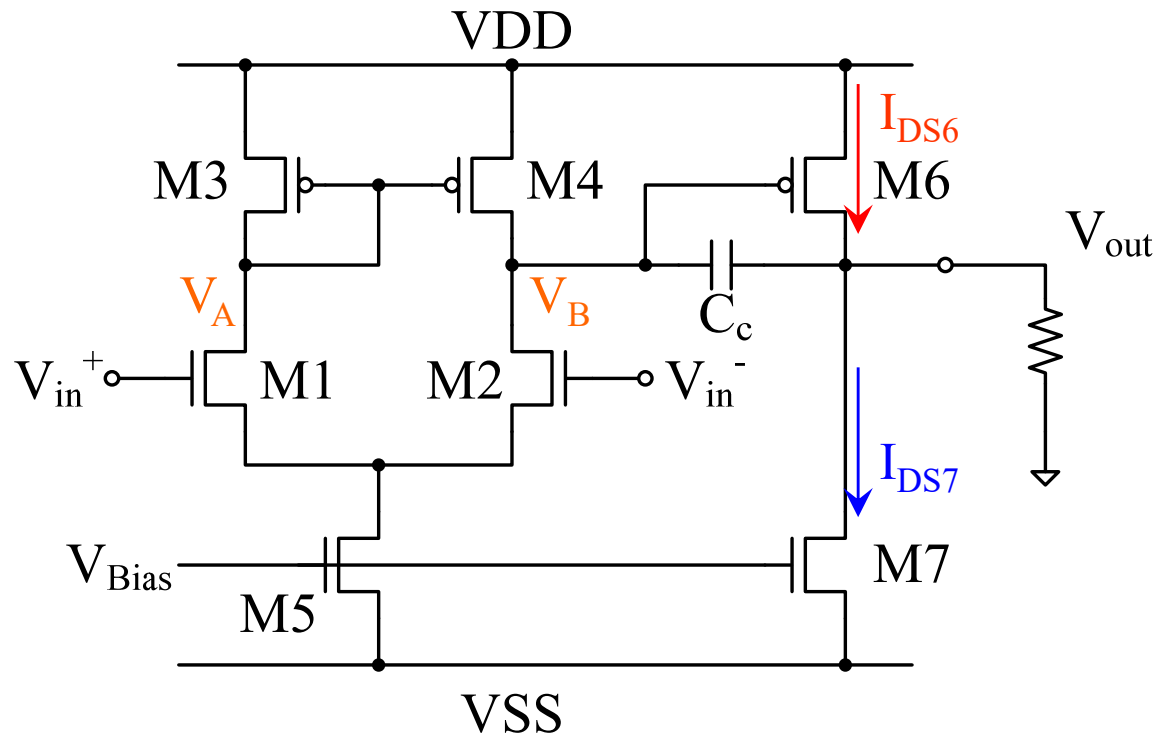
$$\frac{I_{DS6}}{I_{DS4}} = 2 \frac{I_{DS7}}{I_{DS5}}$$

Saturation condition of M4

$$\frac{\left(\frac{W}{L}\right)_6}{\left(\frac{W}{L}\right)_4} = 2 \frac{\left(\frac{W}{L}\right)_7}{\left(\frac{W}{L}\right)_5}$$



# Systematic offset (1)



Systematic offset

Current balance of M6 and M7

Random offset

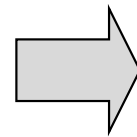
Process variation of  $V_T$

When  $V_A = V_B$  ( differential input = 0),  
the output current = 0 or  $I_{DS6} = I_{DS7}$ .

# Systematic offset (2)

$$\left. \begin{aligned}
 I_{DS3} &= \frac{\beta_3}{2} (V_A - V_{Tp})^2 \\
 I_{DS5} &= \frac{\beta_5}{2} (V_{Bias} - V_{Tn})^2 \\
 I_{DS6} &= \frac{\beta_6}{2} (V_B - V_{Tp})^2 \\
 I_{DS7} &= \frac{\beta_7}{2} (V_{Bias} - V_{Tn})^2 \\
 \\
 \text{When } V_A &= V_B, \\
 \left\{ \begin{aligned}
 I_{DS6} &= I_{DS7} \leftarrow \text{slide 26} \\
 I_{DS3} &= \frac{I_{DS5}}{2}
 \end{aligned} \right.
 \end{aligned} \right\}$$

This constraint is same as the saturation constraint of M4.

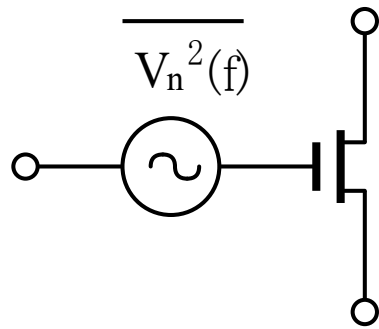


$$\frac{\beta_6}{\beta_3} = 2 \frac{\beta_7}{\beta_5}$$

$$\frac{\left(\frac{W}{L}\right)_6}{\left(\frac{W}{L}\right)_4} = 2 \frac{\left(\frac{W}{L}\right)_7}{\left(\frac{W}{L}\right)_5}$$

# Input-referred noise (1)

## Channel noise model of MOSFET



Thermal noise    Flicker noise

$$\overline{V_n^2(f)} = 4kT\gamma \frac{g_{ds}}{g_m^2} + \frac{K_{p/n}}{WLC_{OX}^2} \frac{1}{f} \quad (V^2 / Hz)$$

$$\left\{ \begin{array}{l} \gamma = 2/3 \text{ (Long Channel)} \\ 1 \text{ (Short Channel)} \end{array} \right.$$

$$\left\{ \begin{array}{l} K_p \cong 10^{-24} \quad (V^2 / F) \\ K_n \cong 10^{-23} \quad (V^2 / F) \end{array} \right.$$

The channel noise is observed in the output terminal, but the noise PSD is normally described as an input-referred noise PSD.

NOTE: Large L is better for the low noise amplifier, because of large L\*W.

# Input-referred noise (2)

Intrinsic noise density of the differential amplifier

$$\left\{ \begin{array}{l} \text{Thermal noise} \\ \text{Flicker noise} \end{array} \right. \quad \overline{V_n^2(f)} = 4kT \left( \frac{1}{g_{m1}} + \frac{g_{m3}}{g_{m1}^2} \right) \quad (\text{Total noise from M1 and M3})$$
$$\overline{V_n^2(f)} = \frac{K_n}{W_1 L_1 C_{OX}^2} \left( 1 + \frac{K_p}{K_n} \frac{W_1 L_1}{W_3 L_3} \right) \frac{1}{f}$$

NOTE: Assuming that the differential pair consists n-ch MOFET and current mirror load consists p-ch MOSFETs.

# Mismatch of MOSFETs by the process variation

$$V_{OS_{1-2}} = V_{GS1} - V_{GS2}$$

$$= V_{Tn1} + \sqrt{\frac{I_{DS5}}{\beta_1}} - V_{Tn2} - \sqrt{\frac{I_{DS5}}{\beta_2}}$$

$$= (V_{Tn1} - V_{Tn2}) + \sqrt{\frac{I_{DS5}}{\beta_1}} \left[ 1 - \sqrt{\frac{\beta_1}{\beta_2}} \right]$$

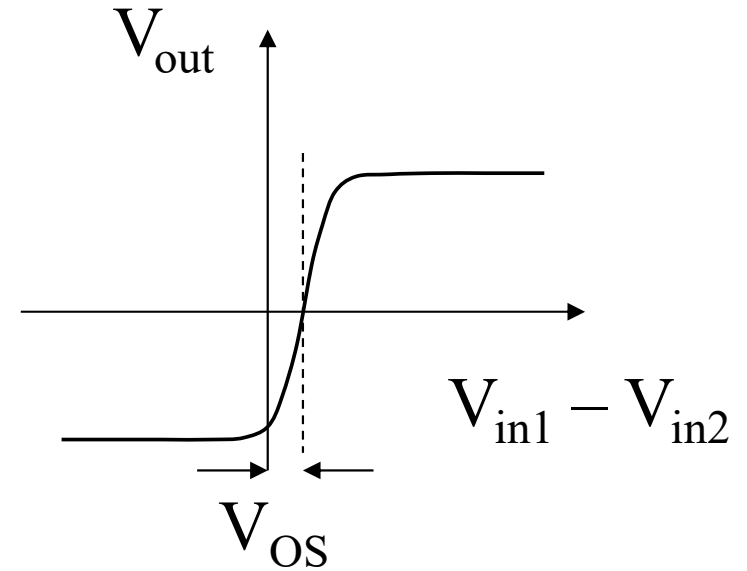
$$\cong (V_{Tn1} - V_{Tn2}) - \frac{1}{2} \sqrt{\frac{I_{DS5}}{\beta_1}} \left[ \frac{\beta_1 - \beta_2}{\beta_1} \right]$$

$$= \Delta V_{Tn1-2} - \frac{V_{GS1} - V_{Tn1}}{2} \left[ \frac{\Delta\beta}{\beta_1} \right]_{1-2} = \Delta V_{Tn1-2} - \frac{\Delta_{OV1}}{2} \left[ \frac{\Delta\beta}{\beta_1} \right]_{1-2}$$

$$V_{OS_{3-4}} = V_{GS3} - V_{GS4}$$

$$\cong \Delta V_{Tn3-4} - \frac{V_{GS3} - V_{Tp3}}{2} \left[ \frac{\Delta\beta}{\beta_3} \right]_{3-4} = \Delta V_{Tn3-4} - \frac{\Delta_{OV3}}{2} \left[ \frac{\Delta\beta}{\beta_3} \right]_{3-4}$$

$$V_{OS} = \Delta V_{Tn1-2} - \frac{\Delta_{OV1}}{2} \left[ \frac{\Delta\beta}{\beta_1} \right]_{1-2} + \frac{g_{m3}}{g_{m1}} \left[ \Delta V_{Tn3-4} - \frac{\Delta_{OV3}}{2} \left[ \frac{\Delta\beta}{\beta_3} \right]_{3-4} \right]$$

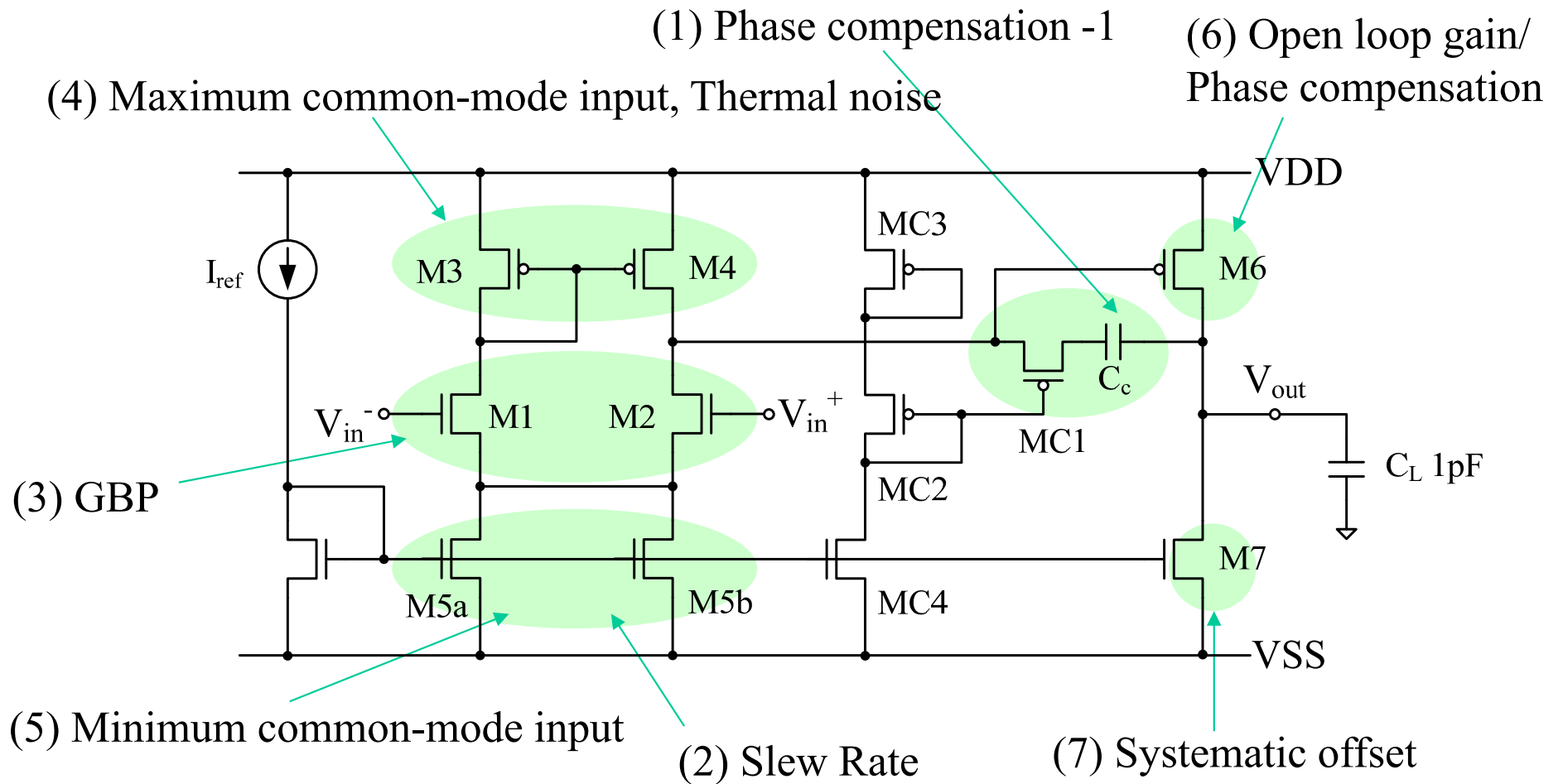


# Optimization for the noise and process variation

- Thermal noise
  - Differential pair MOSFETs: Large  $W/L$
  - Current mirror load MOSFETs: Small  $W/L$
- Flicker noise
  - Differential pair MOSFETs: Large  $W*L$
  - Current mirror load MOSFETs: Large  $W*L$
- Mismatch offset
  - Differential pair MOSFETs: Large  $W, L$
  - Current mirror load MOSFETs: Small  $W/L$  (Small  $g_{m3}/g_{m1}$ )

NOTE: Consider that the  $L$  and  $W$  influences the frequency response too.

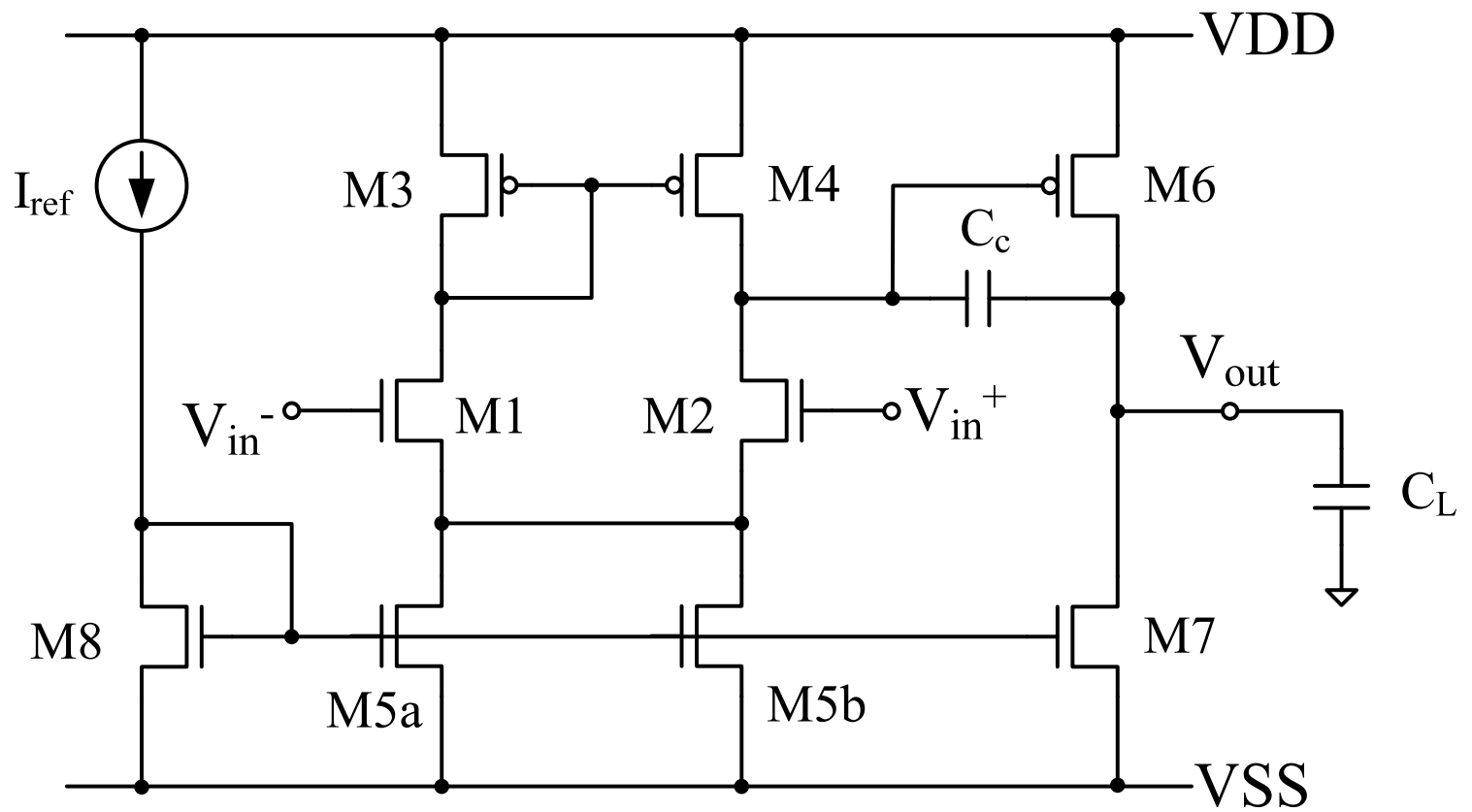
# Design constraints





# 12.4 Design example of a single-end OPA

# Circuit topology



2 stage OPA without zero-canceling

# Specification

---

Power supply voltage	VDD/VSS	2.5V/-2.5V
Open loop gain	Ad	> 95dB
GBP	$f_u$	100MHz
Phase margin	PM	60°
Slew rate	SR	> 100 V/us
Load capacitance	$C_L$	1.0 pF
Output voltage swing	$V_{out_{p-p}}$	> 4.2 V
Maximum common-mode voltage	$V_{in}^{max}$	> 2.1 V
Minimum common-mode voltage	$V_{in}^{min}$	< -1.4 V
Input-referred noise	$\sqrt{v_n^2}$	< 500 uV (BW=1Hz~1MHz)
Power consumption	PW	< 10 mW

---

# Parameters of MOSFET

Parameter	n-ch	p-ch
$V_T$ [V]	0.78	-0.86
$\mu C_{OX}$ [A/V <sup>2</sup> ]	98u	33u
$\lambda$ [1/V]	0.0186	0.0114

The parameters are extracted from 10um/2um MOSFETs for  $\Delta_{OV} = 0.2V$ .

# $C_C, I_{SS}$

## (1) Phase compensation -1

$$\begin{cases} \text{Load capacitance} & C_L = 1.0 \text{ pF} \\ \text{Phase compensation constraint} & C_C \geq 0.2C_L \end{cases}$$

$$C_C = 0.2 \text{ pF}$$

## (2) SR

$$SR = \frac{I_{DS5}}{C_C}$$

$$I_{DS5} = SR \cdot C_C = 100 \text{ MV/s} \cdot 0.2 \text{ pF} = 20 \text{ uA}$$

$$I_{DS3} = I_{DS4} = I_{DS1} = I_{DS2} = \frac{I_{DS5}}{2} = 10 \text{ uA}$$

# M1, M2

## (3) GBP

$$\omega_u = \frac{g_{m1}}{C_C}$$

$$g_{m1} = C_C \omega_u = 0.2\text{p} \cdot 2\pi \cdot 100\text{M} = 126\text{uS}$$

## (2) $I_{DS1}$ & (3) $g_{m1}$

$$g_{m1} = \sqrt{2\beta_1 I_{DS1}} = \sqrt{2\mu_n C_{OX} \left(\frac{W}{L}\right)_1 I_{DS1}} = 126\text{uS}$$

$$\left(\frac{W}{L}\right)_1 = \left(\frac{W}{L}\right)_2 = \frac{g_{m1}^2}{2\mu_n C_{OX} I_{DS1}} = \frac{(126\text{u})^2}{2 \cdot 98\text{u} \cdot 10\text{u}} = 8.1 \approx 10$$

$$\Delta_{OV} = \sqrt{\frac{2I_{DS1}}{\beta_1}} = \sqrt{\frac{2 \cdot 10\text{u}}{98\text{u} \cdot 10}} = 0.143\text{V}$$

# M3, M4

## (4) Maximum common-mode input

$$\begin{cases} V_{in}^{\max} = VDD - \Delta_{OV3} - |V_{Tp}| + V_{Tn} \\ \Delta_{OV3} = \sqrt{\frac{2I_{DS3}}{\beta_3}} = VDD - |V_{Tp}| + V_{Tn} - V_{in}^{\max} \end{cases}$$

$$\beta_3 = \frac{2I_{DS3}}{(VDD - |V_{Tp}| + V_{Tn} - V_{in}^{\max})^2}$$

$$\begin{aligned} \left(\frac{W}{L}\right)_3 &= \left(\frac{W}{L}\right)_4 = \frac{2I_{DS3}}{\mu_p C_{OX}} \frac{1}{(VDD - |V_{Tp}| + V_{Tn} - V_{in}^{\max})^2} \\ &= \frac{2 \cdot 10\text{u}}{33\text{u}} \frac{1}{(2.5 - 0.86 + 0.78 - 2.1)^2} = 5.9 \approx 6 \end{aligned}$$

# M5

## (5) Minimum common-mode input

$$\begin{cases} V_{in}^{\min} = V_{SS} + V_{Tn} + \Delta_{OV1} + \Delta_{OV5} \\ \Delta_{OV5} = \sqrt{\frac{2I_{DS5}}{\beta_5}} = V_{in}^{\min} - \Delta_{OV1} - V_{Tn} - V_{SS} \end{cases}$$

$$\Delta_{OV1} = \sqrt{\frac{2I_{DS1}}{\beta_1}} = \sqrt{\frac{2 \cdot 10\text{u}}{98\text{u} \cdot 10}} = 0.143\text{V}$$

$$\beta_5 = \frac{2I_{DS5}}{(V_{in}^{\min} - \Delta_{OV1} - V_{Tn} - V_{SS})^2}$$

$$\begin{aligned} \left(\frac{W}{L}\right)_5 &= \frac{2I_{DS5}}{\mu_n C_{OX}} \frac{1}{(V_{in}^{\min} - \Delta_{OV1} - V_{Tn} - V_{SS})^2} \\ &= \frac{2 \cdot 10\text{u}}{98\text{u}} \frac{1}{(-1.4 - 0.143 - 0.78 + 2.5)^2} = 6.51 \approx 8 \end{aligned}$$



# M6 (without zero cancellation)

## (6) Phase compensation -2

$$\begin{aligned}
 g_{m6} &\geq 10g_{m1} \\
 &= 10 \cdot \sqrt{2\beta_1 I_{DS1}} \\
 &= 10 \cdot \sqrt{2 \cdot 98\mu \cdot 10 \cdot 10\mu} \\
 &= 1.40\text{mS}
 \end{aligned}$$

If  $V_{GS4} = V_{GS6}$ ,

$$\frac{I_{DS6}}{I_{DS4}} = \frac{\beta_6}{\beta_4}$$

$$g_{m6} = \sqrt{2\beta_6 I_{DS6}}$$

$$\beta_6 = g_{m6} \sqrt{\frac{\beta_4}{2I_{DS4}}}$$

Bias condition:

$$I_{DS6} = \frac{\beta_6}{\beta_4} I_{DS4} = \frac{138}{6} 10\mu = 230\mu\text{A}$$

$$\Delta_{OV6} = \sqrt{\frac{2I_{DS6}}{\beta_6}} = \sqrt{\frac{2 \cdot 230\mu}{33\mu \cdot 138}} = 0.318\text{V}$$

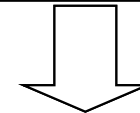
$$\begin{aligned}
 \left(\frac{W}{L}\right)_6 &= \frac{g_{m6}}{\mu_p C_{OX}} \sqrt{\frac{\beta_4}{2I_{DS4}}} \\
 &= \frac{1.40\text{m}}{33 \cdot 10^{-6}} \sqrt{\frac{33\mu \cdot 6}{2 \cdot 10\mu}} \\
 &= 133.48 \approx 138
 \end{aligned}$$

# M7

## (7) Systematic offset (Saturation of M4)

$$\begin{aligned}\left(\frac{W}{L}\right)_7 &= \frac{1}{2} \left(\frac{W}{L}\right)_5 \frac{\left(\frac{W}{L}\right)_6}{\left(\frac{W}{L}\right)_4} \\ &= \frac{1}{2} 8 \frac{138}{6} = 92\end{aligned}$$

The circuit parameters are determined. Check the other specification.



# Output swing

$$\begin{aligned}V_{out}^{\min} &= VSS + \Delta_{OV7} = VSS + \sqrt{\frac{2I_{DS7}}{\mu_n C_{OX} \left(\frac{W}{L}\right)_7}} \\ &= -2.5 + \sqrt{\frac{2 \cdot 230\mu}{98\mu \cdot 92}} \\ &\approx -2.27\text{V}\end{aligned}$$

$$\begin{aligned}V_{out}^{\max} &= VDD - \Delta_{OV6} \\ &= VDD - \sqrt{\frac{2I_{DS6}}{\mu_p C_{OX} \left(\frac{W}{L}\right)_6}} \\ &= 2.5 - \sqrt{\frac{2 \cdot 230\mu}{33\mu \cdot 138}} \\ &\approx 2.18 \text{ V}\end{aligned}$$

Output voltage swing  $V_{out, p-p} = 4.45 \text{ V}$

# Open loop gain

$$\begin{aligned}A_d &= A_{V1} \cdot A_{V2} \\&= g_{m1}(r_{ds2} // r_{ds4}) \cdot g_{m6}(r_{ds6} // r_{ds7}) \\&= \frac{\sqrt{2\beta_1 I_{DS1}}}{I_{DS1}(\lambda_n + \lambda_p)} \cdot \frac{\sqrt{2\beta_6 I_{DS6}}}{I_{D6}(\lambda_n + \lambda_p)} \\&= \frac{\sqrt{\frac{2 \cdot 98\mu \cdot 10}{10\mu}}}{(0.0186 + 0.114)} \cdot \frac{\sqrt{\frac{2 \cdot 33\mu \cdot 138}{230\mu}}}{(0.0186 + 0.0114)} \\&= 466 \cdot 210 \\&= 97749 = 99.8\text{dB}\end{aligned}$$

# Flicker noise (1)

$$V_{nf}^2 = \frac{K_n}{W_1 L_1 C_{OX}^2} \left\{ 1 + \frac{K_p}{K_n} \frac{W_1 L_1}{W_3 L_3} \right\} \frac{1}{f} \quad (\text{V}^2/\text{Hz})$$

$$NL_f^2 = \int_{f_l}^{f_u} V_{nf}^2 df = \frac{K_n}{W_1 L_1 C_{OX}^2} \left( 1 + \frac{K_p}{K_n} \frac{W_1 L_1}{W_3 L_3} \right) \ln(f_u / f_l) \quad (\text{frequency range } f_u \sim f_u)$$

$$= \frac{K_n}{W_1 L_1 C_{OX}^2} \left( 1 + \frac{K_p}{K_n} \frac{W_1}{W_3} \right) \ln(f_u / f_l) \quad (\text{for } L_1 = L_3)$$

$$C_{OX} = \frac{\epsilon_0 \epsilon_{Si}}{t_{OX}} = 2.5 \cdot 10^{-3} \text{ F/m}^2$$

The parameter  $C_{OX}$  can be loosely estimated for  $\mu_n C_{OX}$  or  $\mu_p C_{OX}$ .  
 Say  $\mu_n \sim 400 \text{ cm}^2/\text{Vs}$  and  $\mu_p \sim 130 \text{ cm}^2/\text{Vs}$ .

# Flicker noise (2)

Based on the specification sheet, at  $f_u = 1$  MHz,  $V_{\text{nf}} = 500 \mu\text{V}$ .

$$(500\mu\text{V})^2 \geq NL_f^2$$

$$2.5 \cdot 10^{-7} \geq \frac{10^{-24}}{W_1 L_1 \cdot (2.5 \cdot 10^{-3})^2} \left(1 + 0.1 \frac{10}{6}\right) \ln(1 \cdot 10^6 / 1 \cdot 10^{-1}) \quad \text{V}^2$$
$$= \frac{3.009 \cdot 10^{-18}}{W_1 L_1}$$

$$\begin{cases} W_1 L_1 \geq 1.203 \cdot 10^{-11} & \text{m}^2 \\ \frac{W_1}{L_1} = 10 \end{cases}$$

$$\therefore L_1 \geq 1.096 \mu\text{m} \quad \longrightarrow \quad L_1 \approx 2 \mu\text{m}$$

# Thermal noise

$$V_{nt}^2 = \frac{8}{3} kT \left( \frac{1}{g_{m1}} + \frac{g_{m3}}{g_{m1}^2} \right) \quad \text{V}^2/\text{Hz}$$

$$NL_t^2 = \frac{8}{3} kT \left( \frac{1}{g_{m1}} + \frac{g_{m3}}{g_{m1}^2} \right) \Delta f \quad (\text{frequency range } 0 \sim f_u)$$

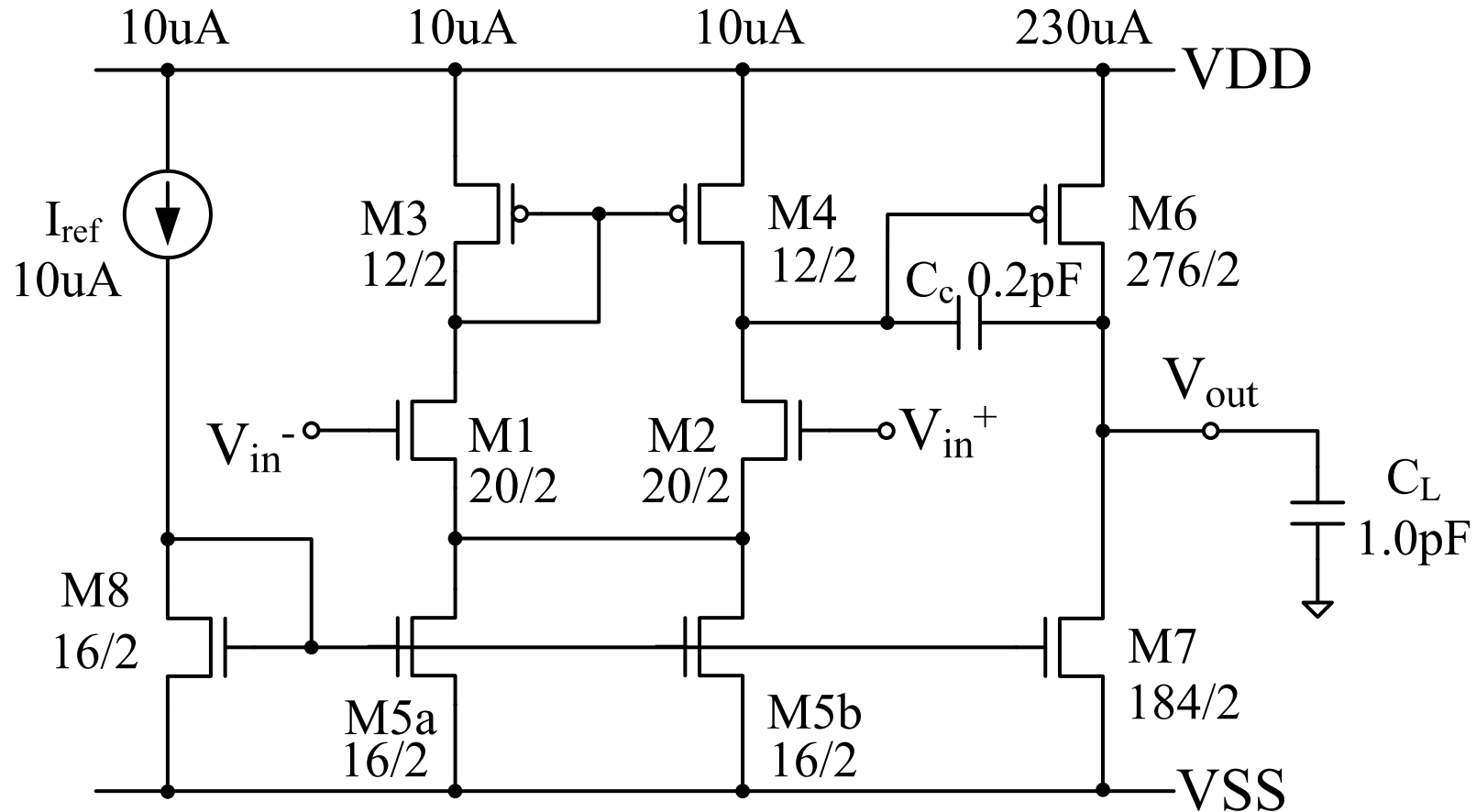
$$\begin{cases} g_{m1} = \sqrt{2\beta_1 I_{D1}} = \sqrt{2 \cdot 98\mu \cdot 10 \cdot 10\mu} \cong 140\mu\text{S} \\ g_{m3} = \sqrt{2\beta_3 I_{D3}} = \sqrt{2 \cdot 33\mu \cdot 6 \cdot 10\mu} \cong 62.9\mu\text{S} \end{cases}$$

at  $T = 300\text{K}$

$$NL_t^2 = \frac{8}{3} 1.38 \cdot 10^{-23} \cdot 300 \frac{1}{140\mu} \left( 1 + \frac{62.9\mu}{140\mu} \right) \Delta f \leq (500\mu\text{V})^2$$

$$\Delta f \leq 2.187\text{GHz} > 1.0\text{MHz}$$

# Completion



Power consumption  $P_w = (230\mu + 3 \cdot 10\mu) \cdot 5.0V = 1.3 \text{ mW}$